



STW50NB20

N - CHANNEL 200V - 0.047Ω - 50A - TO-247 PowerMESH™ MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW50NB20	200 V	< 0.055 Ω	50A

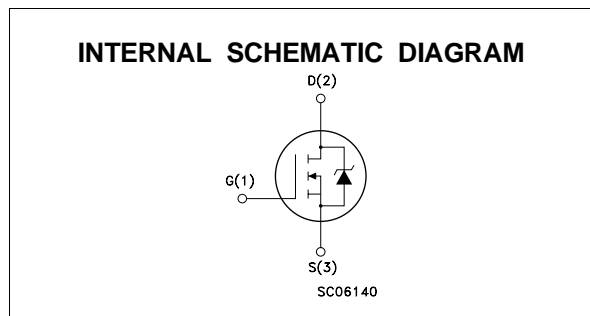
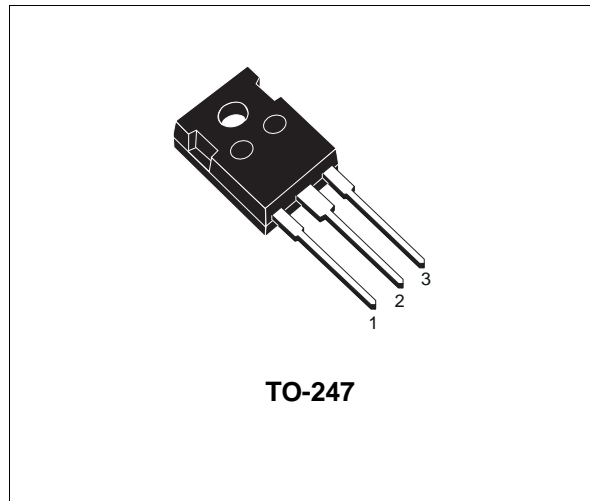
- TYPICAL R_{DS(on)} = 0.047 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE
- HIGH CURRENT, HIGH SPEED SWITCHING



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	200	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	200	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	50	A
I _D	Drain Current (continuous) at T _c = 100 °C	32	A
I _{DM} (●)	Drain Current (pulsed)	200	A
P _{tot}	Total Dissipation at T _c = 25 °C	280	W
	Derating Factor	2.24	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 50A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

STW50NB20

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.44	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	50	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	1000	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	200			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 25 A		0.047	0.055	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	50			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 25 A	10	17		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		3400	4600	pF
C _{oss}	Output Capacitance			900	1250	pF
C _{rss}	Reverse Transfer Capacitance			125	170	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 100\text{ V}$ $I_D = 25\text{ A}$		35	47	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		65	87	ns
Q_g	Total Gate Charge	$V_{DD} = 160\text{ V}$ $I_D = 50\text{ A}$ $V_{GS} = 10\text{ V}$		84	115	nC
Q_{gs}	Gate-Source Charge			26		nC
Q_{gd}	Gate-Drain Charge			44		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 160\text{ V}$ $I_D = 50\text{ A}$		18	25	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		27	37	ns
t_c	Cross-over Time			50	68	ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				50	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)					A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 50\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 50\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		330		ns
Q_{rr}	Reverse Recovery Charge			3.5		μC
I_{RRM}	Reverse Recovery Current			21		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 1998 STMicroelectronics – Printed in Italy – All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.